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(54) Title: WET CLEANING OF CHAMBER COMPONENT

(57) Abstract: Embodiments of the invention generally provide methods for cleaning a UV processing chamber component. In one embodiment, a method for cleaning a UV processing chamber component includes soaking the chamber component having a SiCO residue formed thereon in a cleaning solution for about 1 to 10 minutes. The cleaning solution comprises about 5% by weight to about 60% weight of NH4F and about 0.5% by weight to about 10% by weight of HF. The method also includes polishing the chamber component. In another embodiment, a method of cleaning a processing chamber component fabricated from quartz includes soaking the chamber component having a SiCO residue formed thereon in a cleaning solution comprising about 36% by weight of NH4F and about 5% by weight of HF for about 3 minutes. The method also includes applying an ultrasonic power to the cleaning solution, and mechanically polishing the chamber component.

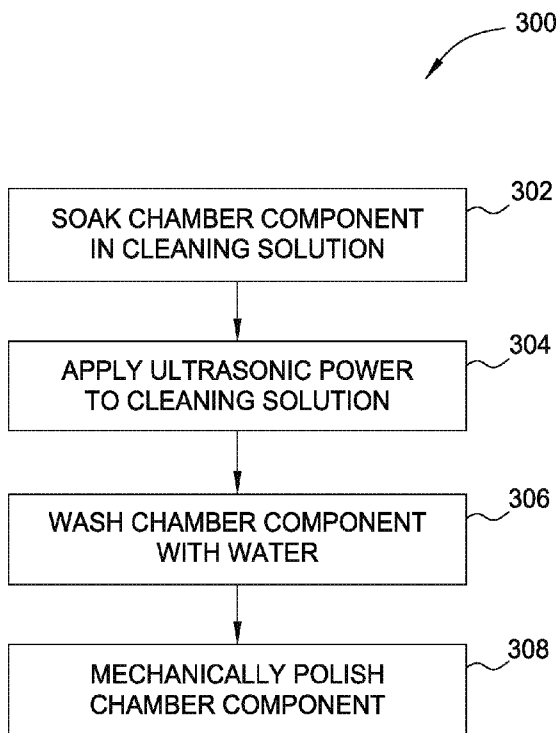


FIG. 3

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